

## HiPerFRED

$$V_{RRM} = 300\text{ V}$$

$$I_{FAV} = 10\text{ A}$$

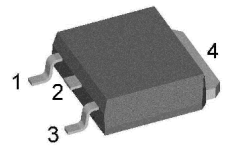
$$t_{rr} = 35\text{ ns}$$

High Performance Fast Recovery Diode  
Low Loss and Soft Recovery  
Single Diode

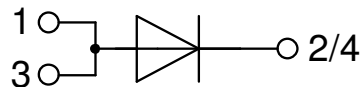
Part number

**DPG10IM300UC**

Marking on Product: PAOGUI



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

#### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

#### Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms .Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

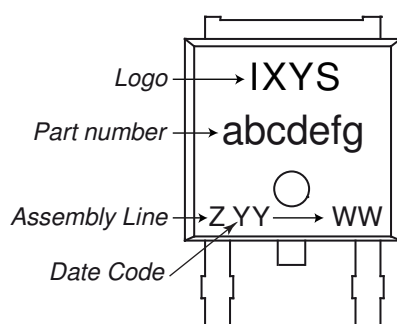
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings					
Symbol	Definition	Conditions		min.	typ.	max.	Unit		
V <sub>RSM</sub>	max. non-repetitive reverse blocking voltage	T <sub>VJ</sub> = 25°C				300	V		
V <sub>RRM</sub>	max. repetitive reverse blocking voltage	T <sub>VJ</sub> = 25°C				300	V		
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 300 V	T <sub>VJ</sub> = 25°C			1	μA		
		V <sub>R</sub> = 300 V	T <sub>VJ</sub> = 150°C			0.06	mA		
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 10 A	T <sub>VJ</sub> = 25°C			1.27	V		
		I <sub>F</sub> = 20 A				1.45	V		
		I <sub>F</sub> = 10 A	T <sub>VJ</sub> = 150°C			0.98	V		
		I <sub>F</sub> = 20 A				1.17	V		
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 150°C rectangular      d = 0.5	T <sub>VJ</sub> = 175°C			10	A		
V <sub>F0</sub>	threshold voltage	} for power loss calculation only		T <sub>VJ</sub> = 175°C		0.74	V		
r <sub>F</sub>	slope resistance					17.7	mΩ		
R <sub>thJC</sub>	thermal resistance junction to case					2.3	K/W		
R <sub>thCH</sub>	thermal resistance case to heatsink				0.50		K/W		
P <sub>tot</sub>	total power dissipation	T <sub>C</sub> = 25°C				65	W		
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine; V <sub>R</sub> = 0 V		T <sub>VJ</sub> = 45°C		140	A		
C <sub>J</sub>	junction capacitance	V <sub>R</sub> = 150 V   f = 1 MHz		T <sub>VJ</sub> = 25°C	15		pF		
I <sub>RM</sub>	max. reverse recovery current	} I <sub>F</sub> = 10 A; V = 200 V -d F/dt = 200 A/μs		T <sub>VJ</sub> = 25 °C	3		A		
				T <sub>VJ</sub> = 125°C	5.5		A		
t <sub>rr</sub>	reverse recovery time			T <sub>VJ</sub> = 25 °C	35		ns		
				T <sub>VJ</sub> = 125 °C	45		ns		

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			20	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
Weight				0.3		g
$F_c$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

### Product Marking



### Part description

D = Diode  
 P = HiPerFRED  
 G = extreme fast  
 10 = Current Rating [A]  
 IM = Single Diode  
 300 = Reverse Voltage [V]  
 UC = TO-252AA (DPak)

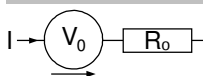
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG10IM300UC	PAOGUI	Tape & Reel	2500	505682

Similar Part	Package	Voltage class
DPG10I300PA	TO-220AC (2)	300

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 175^\circ\text{C}$



$V_{0\max}$  threshold voltage

$R_{0\max}$  slope resistance \*

Fast Diode

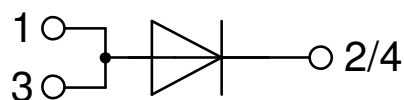
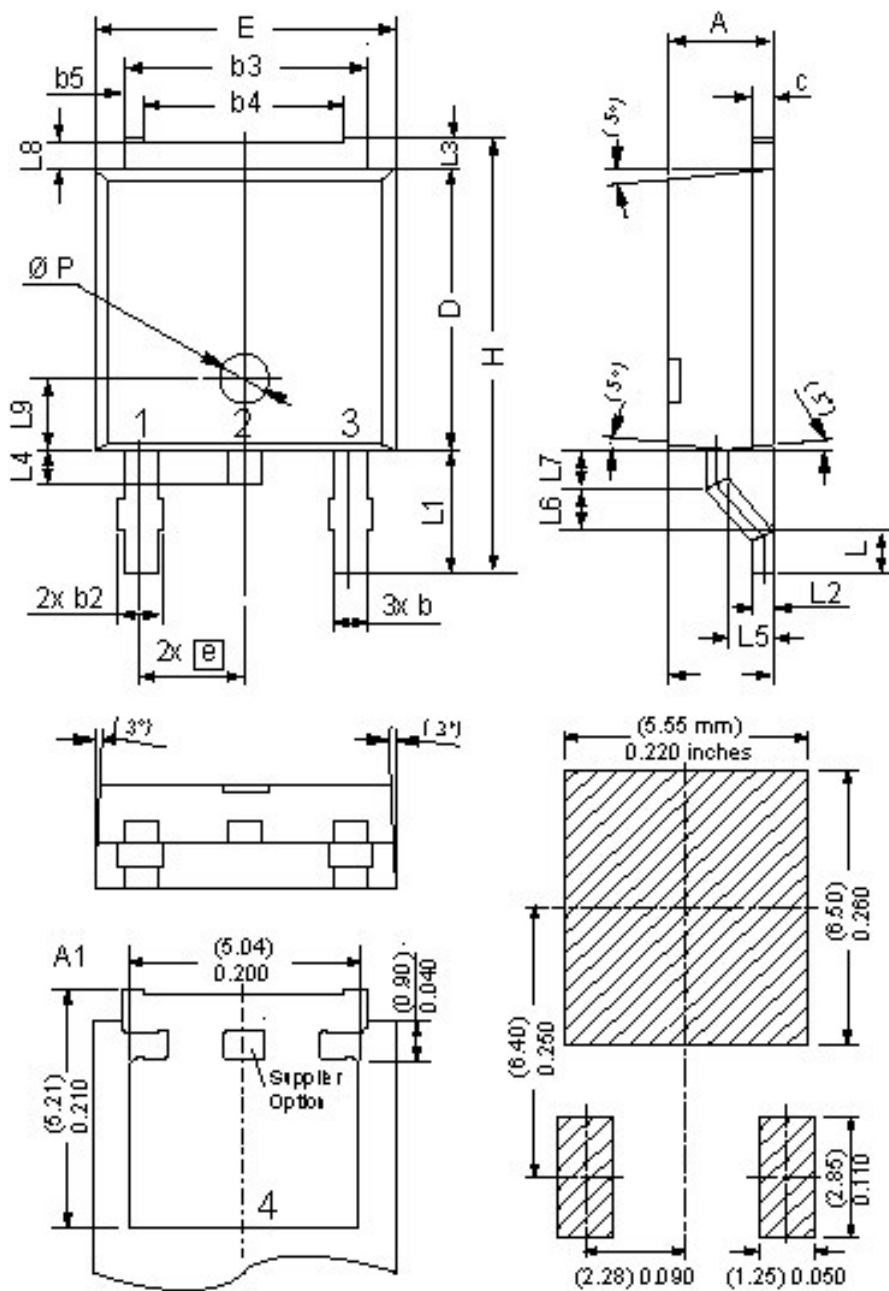
0.74

14.5

V

mΩ

## Outlines TO-252 (DPak)



## Fast Diode

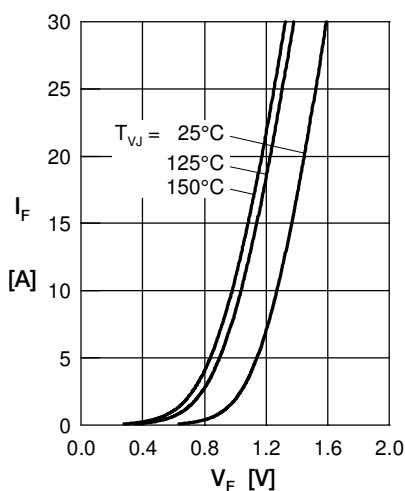


Fig. 1 Forward current  $I_F$  versus  $V_F$

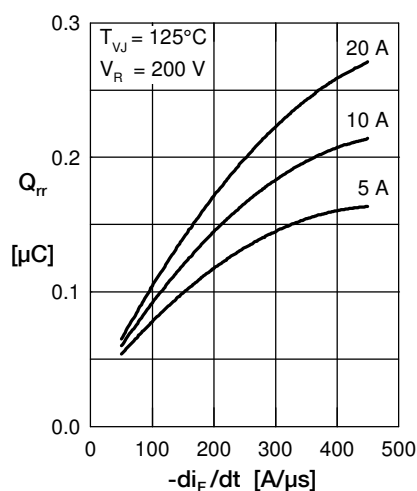


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$

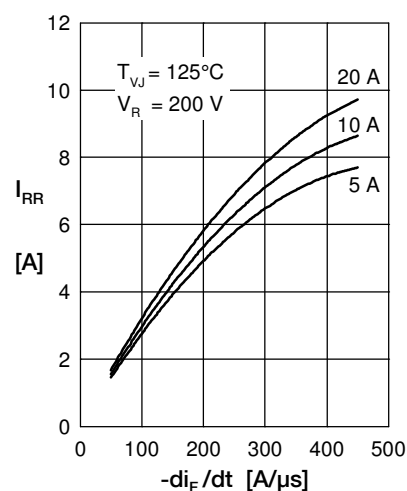


Fig. 3 Typ. reverse recov. current  $I_{RR}$  versus  $-di_F/dt$

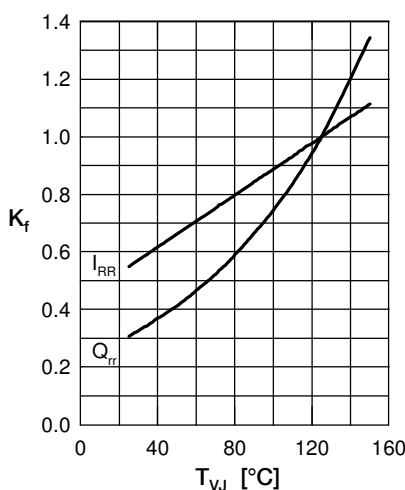


Fig. 4 Typ. dynamic parameters  $Q_{rr}$ ,  $I_{RR}$  versus  $T_{VJ}$

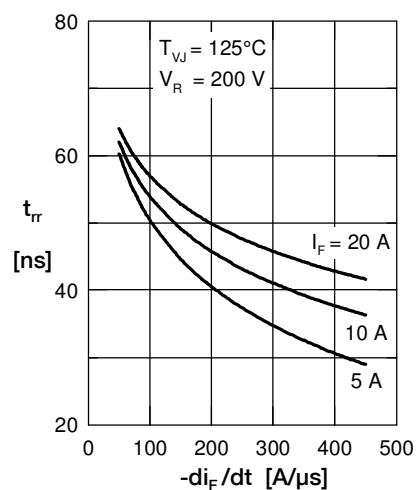


Fig. 5 Typ. reverse recov. time  $t_{rr}$  versus  $-di_F/dt$

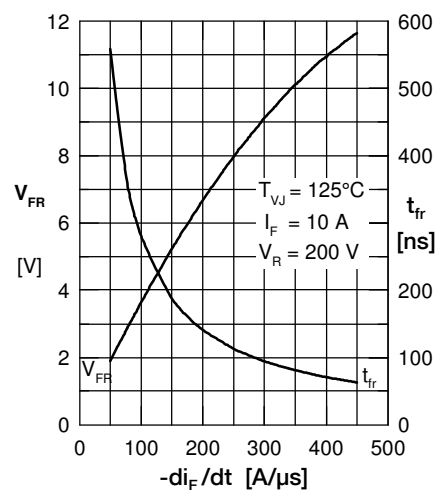


Fig. 6 Typ. forward recov. voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

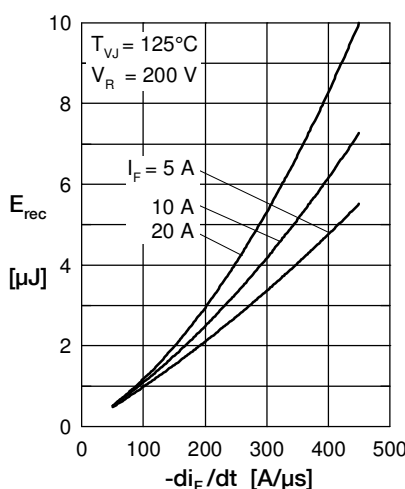


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

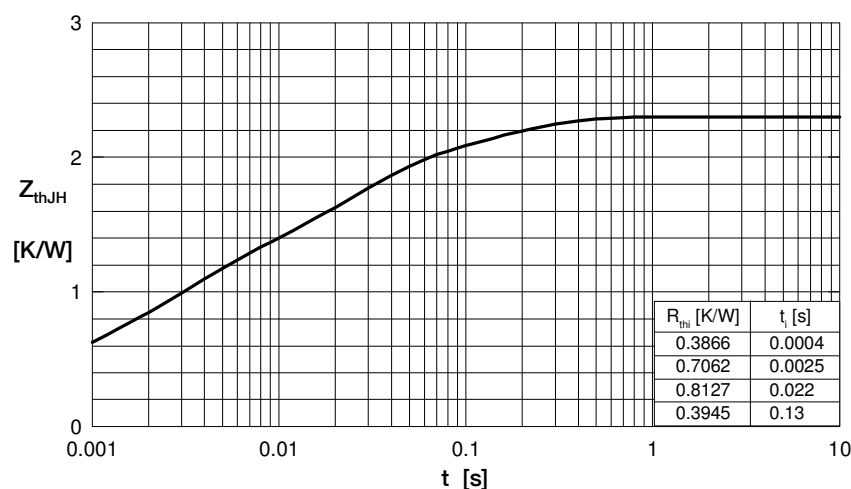


Fig. 8 Transient thermal resistance junction to case